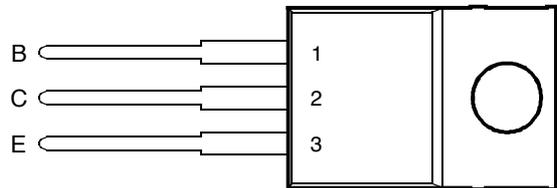


BD543, BD543A, BD543B, BD543C NPN SILICON POWER TRANSISTORS



- Designed for Complementary Use with the BD544 Series
- 70 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- 10 A Peak Collector Current
- Customer-Specified Selections Available

TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRACA



This series is obsolete and not recommended for new designs.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|--|--------|-----------|-------------|------|
| Collector-base voltage ($I_E = 0$) | BD543 | V_{CB0} | 40 | V |
| | BD543A | | 60 | |
| | BD543B | | 80 | |
| | BD543C | | 100 | |
| Collector-emitter voltage ($I_B = 0$) | BD543 | V_{CE0} | 40 | V |
| | BD543A | | 60 | |
| | BD543B | | 80 | |
| | BD543C | | 100 | |
| Emitter-base voltage | | V_{EB0} | 5 | V |
| Continuous collector current | | I_C | 8 | A |
| Peak collector current (see Note 1) | | I_{CM} | 10 | A |
| Continuous device dissipation at (or below) 25°C case temperature (see Note 2) | | P_{tot} | 70 | W |
| Continuous device dissipation at (or below) 25°C free air temperature (see Note 3) | | P_{tot} | 2 | W |
| Operating free air temperature range | | T_A | -65 to +150 | °C |
| Operating junction temperature range | | T_j | -65 to +150 | °C |
| Storage temperature range | | T_{stg} | -65 to +150 | °C |
| Lead temperature 3.2 mm from case for 10 seconds | | T_L | 260 | °C |

- NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002
 Specifications are subject to change without notice.

electrical characteristics at 25°C case temperature

| PARAMETER | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|--|---|---|-------------------------------------|-----------------------|-----|--------------------------|------|
| $V_{(BR)CEO}$ Collector-emitter breakdown voltage | $I_C = 30 \text{ mA}$ (see Note 4) | $I_B = 0$ | BD543 BD543A BD543B BD543C | 40 60 80 100 | | | V |
| I_{CES} Collector-emitter cut-off current | $V_{CE} = 40 \text{ V}$ $V_{CE} = 60 \text{ V}$ $V_{CE} = 80 \text{ V}$ $V_{CE} = 100 \text{ V}$ | $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ | BD543 BD543A BD543B BD543C | | | 0.4 0.4 0.4 0.4 | mA |
| I_{CEO} Collector cut-off current | $V_{CE} = 30 \text{ V}$ $V_{CE} = 60 \text{ V}$ | $I_B = 0$ $I_B = 0$ | BD543/543A BD543B/543C | | | 0.7 0.7 | mA |
| I_{EBO} Emitter cut-off current | $V_{EB} = 5 \text{ V}$ | $I_C = 0$ | | | | 1 | mA |
| h_{FE} Forward current transfer ratio | $V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$ | $I_C = 1 \text{ A}$ $I_C = 3 \text{ A}$ $I_C = 5 \text{ A}$ | (see Notes 4 and 5) | 60 40 15 | | | |
| $V_{CE(sat)}$ Collector-emitter saturation voltage | $I_B = 0.3 \text{ A}$ $I_B = 1 \text{ A}$ $I_B = 1.6 \text{ A}$ | $I_C = 3 \text{ A}$ $I_C = 5 \text{ A}$ $I_C = 8 \text{ A}$ | (see Notes 4 and 5) | | | 0.5 0.5 1 | V |
| V_{BE} Base-emitter voltage | $V_{CE} = 4 \text{ V}$ | $I_C = 5 \text{ A}$ | (see Notes 4 and 5) | | | 1.4 | V |
| h_{fe} Small signal forward current transfer ratio | $V_{CE} = 10 \text{ V}$ | $I_C = 0.5 \text{ A}$ | $f = 1 \text{ kHz}$ | 20 | | | |
| $ h_{fe} $ Small signal forward current transfer ratio | $V_{CE} = 10 \text{ V}$ | $I_C = 0.5 \text{ A}$ | $f = 1 \text{ MHz}$ | 3 | | | |

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

| PARAMETER | MIN | TYP | MAX | UNIT |
|---|-----|-----|------|------|
| $R_{\theta JC}$ Junction to case thermal resistance | | | 1.79 | °C/W |
| $R_{\theta JA}$ Junction to free air thermal resistance | | | 62.5 | °C/W |

resistive-load-switching characteristics at 25°C case temperature

| PARAMETER | TEST CONDITIONS † | | | MIN | TYP | MAX | UNIT |
|-------------------------|------------------------------|-----------------------------|--|-----|-----|-----|---------------|
| t_{on} Turn-on time | $I_C = 6 \text{ A}$ | $I_{B(on)} = 0.6 \text{ A}$ | $I_{B(off)} = -0.6 \text{ A}$ | | 0.6 | | μs |
| t_{off} Turn-off time | $V_{BE(off)} = -4 \text{ V}$ | $R_L = 5 \Omega$ | $t_p = 20 \mu\text{s}$, dc $\leq 2\%$ | | 1 | | μs |

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
VS
COLLECTOR CURRENT

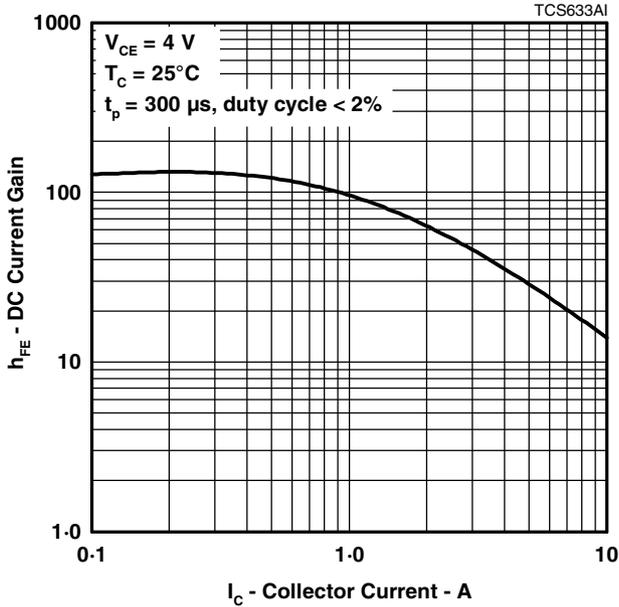


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
VS
BASE CURRENT

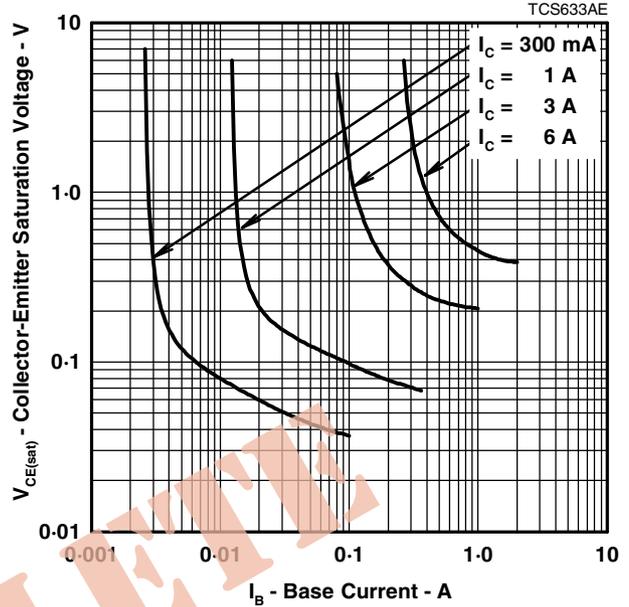


Figure 2.

BASE-EMITTER VOLTAGE
VS
COLLECTOR CURRENT

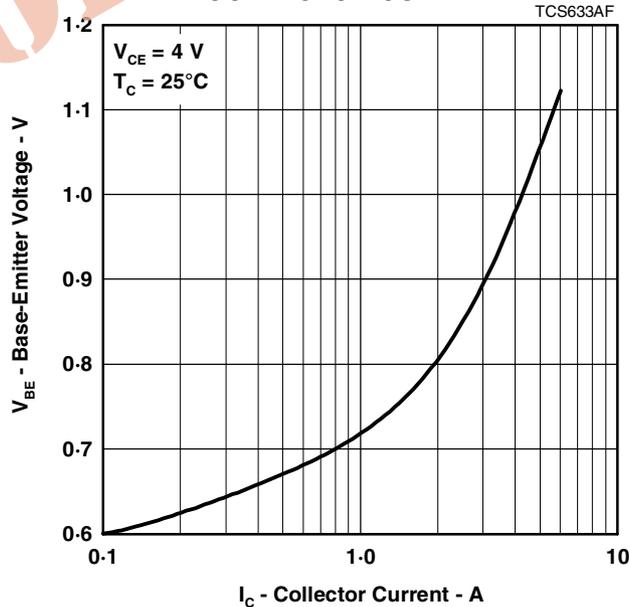


Figure 3.

PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

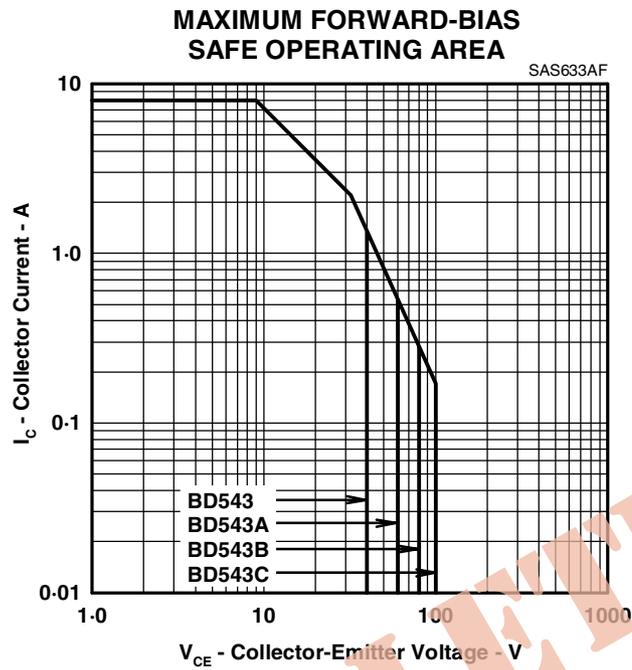


Figure 4.

THERMAL INFORMATION

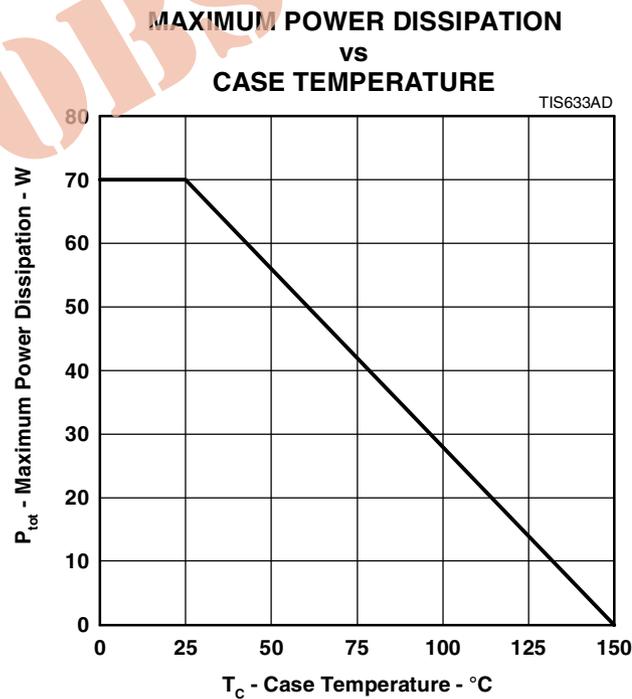


Figure 5.

PRODUCT INFORMATION